

Amendments to Specification

Please replace paragraph [0054] with the following amended paragraph:

[0054] In the invention, the stripping layer may be formed of a metallic material such as chromium, nickel, tantalum or tungsten, an insulating material such as alumina or silicon dioxide, or ~~InZnO~~ IZO and the like. The stripping layer may be formed with vacuum deposition, vapor phase growth, sputtering or the like. The supporting pillar female mold may be formed in the stripping layer with photolithography or the like.

Please replace paragraph [0057] with the following amended paragraph:

[0057] In the invention, the stripping layer formed of, for example, alumina may be removed with a solution of phosphoric acid as a principal component. The stripping layer formed of silicon dioxide may be removed with an etching solution containing hydrofluoric acid, and the stripping layer formed of ~~InZnO~~ IZO may be removed with hydrochloric acid.

Please replace paragraph [0070] with the following amended paragraph:

[0070] ~~InZnO~~ IZO was deposited as the stripping layer 13 with a thickness of 2 μm on the whole surface of a sheet of Corning 1737 glass (a product of Corning) as the temporary substrate 12 with the sputtering method. A supporting pillar female mold was patterned in the stripping layer 13 with the photolithography method. ~~InZnO~~ IZO was further deposited to form a layer with a thickness of 0.2 μm with the sputtering method. Accordingly, as shown in Fig. 3, the stripping layer 13 having the supporting pillar female mold therein was formed on the temporary substrate 12.